

600V, 15A, Trench FS II Fast IGBT

General Description:

Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

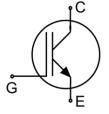
Features

Trench FSII Technology offering

- Very low Vce (sat)
- High speed switching
- Positive temperature coefficient in V_{CE} (sat)
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE15T60BD	TO-263	NCE15T60BD



TO-263

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	600	V
V _{GES}	Gate- Emitter Voltage	±30	V
1-	Collector Current	30	Α
lc	Collector Current @T _C = 100°C	15	Α
I _{Cplus}	Pulsed Collector Current, tp limited by Tjmax	45	Α
-	turn off safe operating area, V _{CE} =600V, T _J =150°C	45	Α
D-	Power Dissipation @ T _C = 25°C	105	W
P _D	Power Dissipation @Tc = 100°C	42	W
T _J ,T _{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
TL	Maximum Temperature for Soldering	260	°C
t _{sc}	Short circuit withstand time V _{GE} =15.0V, V _{CC} ≤400V, Allowed number of short circuits<1000Time between short circuits:≥1.0s,T _j ≤150°C	3	us



NCE15T60BD

Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	1.19	°C/W
Reja	Thermal Resistance, Junction to Ambient	62	°C/W

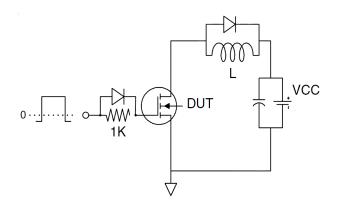
Electrical Characteristics (T_C=25°C unless otherwise noted)

0		Test Conditions		Rating				
Symbol	Parameter	lest Co	nditions	Min.	Тур.	Max.	Units	
Static Chara	cteristics							
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	600			V	
Ices	Collector-Emitter Leakage Current	V _{GE} =0V	,Vce=600V			4	uA	
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30	V,V _{CE} =0V			100	nA	
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30	V,V _{CE} =0V			100	nA	
		I _C =10A,V _{GE} =15V			1.5		V	
$V_{\text{CE(sat)}}$	Collector-Emitter Saturation Voltage	Ic=15A	Tj=25°C		1.7	1.9	V	
		V _{GE} =15V	Tj=100°C		1.9		V	
$V_{\text{GE(th)}}$	Gate Threshold Voltage	I _C =1mA	,V _{CE} =V _{GE}	4.0		6.0	V	
Dynamic Ch	aracteristics							
Cies	Input Capacitance	V _{CE} =25V,V _{GE} =0V, f=1MHz			1635		pF	
Coes	Output Capacitance				50			
Cres	Reverse Transfer Capacitance				30			
Qg	Total Gate Charge				63			
Q _{ge}	Gate to Emitter Charge	Vcc=480V, Ic=15A V _{GE} =15V			15		nC	
Qgc	Gate to Collector Charge	VGE	-10 V		26			
Ic(sc)	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s		V _{CC} ≤400V, ,Tj≤150°C		82		А	
Switching Cl	haracteristics							
t _{d(ON)}	Turn-on Delay Time				16			
tr	Rise Time	Vcc=400V,Ic=10A			12		ns	
t _{d(OFF)}	Turn-Off Delay Time				124			
t _f	Fall Time	V _{GE} =0/1	5V, R _g =5Ω		12			
Eon	Turn-On Switching Loss	Induct	ive Load		0.25			
E _{off}	Turn-Off Switching Loss				0.12		mJ	
Ets	Total Switching Loss				0.37			

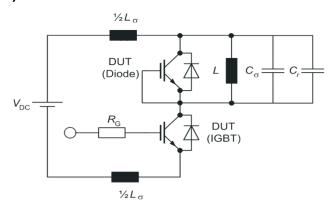


Test Circuit

1) Gate Charge Test Circuit

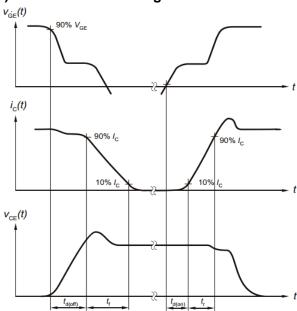


2) Switch Time Test Circuit

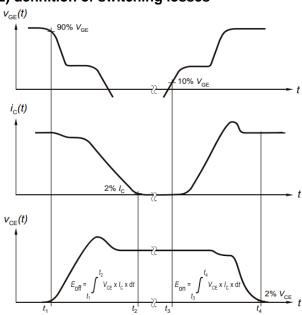


Switching characteristics

1) definition of switching times



2) definition of switching losses





Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

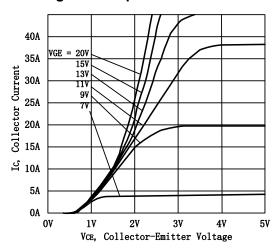


Figure 3 V_{CEsat} vs. Case Temperature

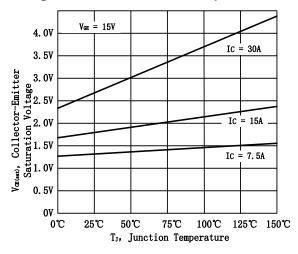


Figure 5 Capacitance Characteristics

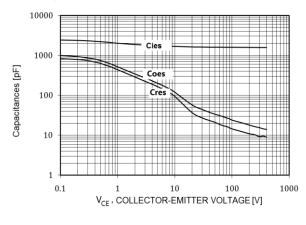


Figure 2 Transfer Characteristics

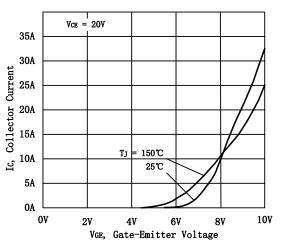


Figure 4 Saturation Voltage vs. VGE

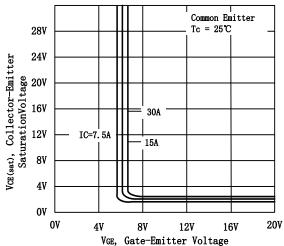


Figure 6 Gate charge waveform

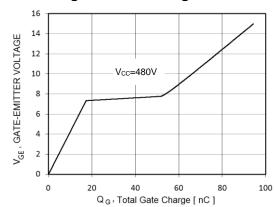




Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

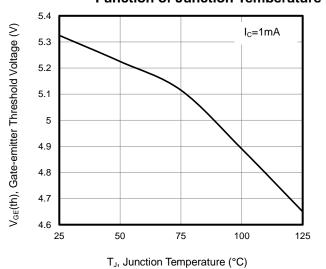


Figure 9 Typical Switching Times as a Function of Junction Temperature

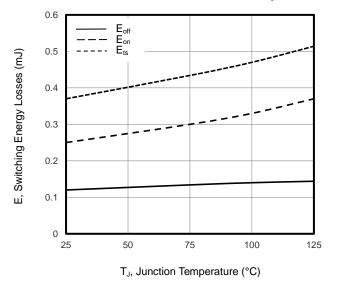


Figure 11 Reverse Bias SOA

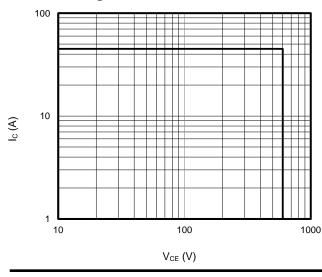


Figure 8 Typical Switching Times as a Function of Gate Resistor

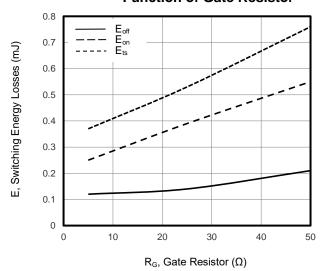


Figure 10 Power Dissipation as a Function of Case Temperature

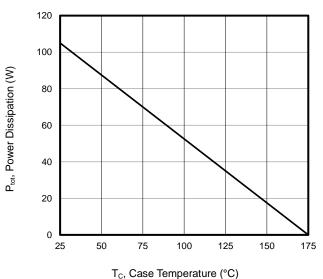
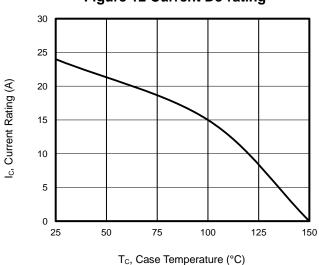
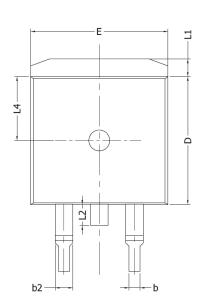


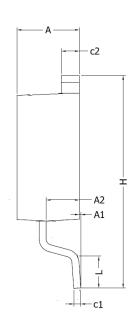
Figure 12 Current De-rating

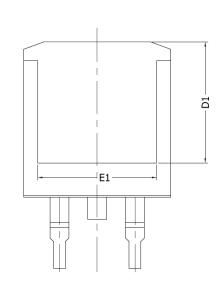




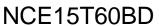
TO-263-3L Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Gymbol	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.17	0.18	
A1	0.00	0.25	0.00	0.01	
A2	2.20	2.60	0.09	0.10	
b	0.76	0.89	0.03	0.04	
b2	1.23	1.37	0.05	0.05	
С	0.47	0.60	0.02	0.02	
c1	0.46	0.56	0.02	0.02	
c2	1.25	1.35	0.05	0.05	
D	0.91	0.93	0.04	0.04	
D1	8.00	-	0.31	-	
Е	9.80	10.00	0.39	0.39	
E1	7.80	-	0.31	-	
е	2.54BSC		0.10	BSC	
Н	14.90	15.70	0.59	0.62	
L	2.00	2.60	0.08	0.10	
L1	1.17	1.40	0.05	0.06	
L2	-	1.75	-	0.07	
L4	4.60REF		0.18	REF	





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